

AMENDMENTS TO THE CLAIMS

1. **(Original)** A light transmitting porous conductive material comprising a porous glass and a conductive oxide film formed on the outer surfaces of the porous glass and on the surfaces inside the pores thereof.

2. **(Original)** The porous conductive material according to claim 1, wherein the resistivity of an outer surface of the porous conductive material is 10^{-4} to $10^4 \Omega \cdot \text{cm}$, the resistance between the two outer surfaces of the porous conductive material is 10^{-4}k to 500 k Ω , and the specific surface area of the porous conductive material is 4 to 600 m^2/g .

3. **(Original)** The porous conductive material according to claim 2, wherein the resistivity of an outer surface of the porous conductive material is 10^{-4} to $10^1 \Omega \cdot \text{cm}$, the resistance between the two outer surfaces of the porous conductive material is 10^{-4}k to 300 k Ω , and the specific surface area of the porous conductive material is 9 to 400 m^2/g .

4. **(Original)** The porous conductive material according to claim 1, wherein the conductive oxide film is constituted by at least one conductive oxides selected from the group consisting of SnO_2 , In_2O_3 , ITO (Sn doped In_2O_3), ZnO , PbO_2 , ZnSb_2O_6 , CdO , CdIn_2O_4 , MgIn_2O_4 , ZnGa_2O_4 , CdGa_2O_4 , Cd_2SnO_4 , Zn_2SnO_4 , Ti_2O_3 , TiOF , Ga_2O_3 , GaInO_3 , Cd_2SnO_4 , CdSnO_3 , In_2TeO_6 , InGaMgO_4 , InGaZnO_4 , $\text{Zn}_2\text{In}_2\text{O}_5$, AgSbO_3 , Cd_2GeO_4 , $\text{Cd}_2\text{Ge}_2\text{O}_7$, ZnSnO_3 , AgInO_2 , CuAlO_2 , CuGaO_2 , SrCu_2O_2 , amorphous In_2O_3 , amorphous CdO-GeO_2 , Sb doped SnO_2 , F doped SnO_2 , In doped ZnO , Ga doped ZnO and Al doped ZnO .

5. **(Original)** The porous conductive material according to claim 4, wherein the conductive oxide film is constituted by at least one conductive oxide selected from the group consisting of SnO_2 , In_2O_3 , ITO, Sb doped SnO_2 and F doped SnO_2 .

6. **(Original)** A Graetzel type solar cell comprising the porous conductive material according to any one of claims 1 to 5 as an electrode material.

7. **(Original)** A photomultiplier comprising the porous conductive material according to any one of claims 1 to 5 as an electrode material.

8. **(Currently amended)** A method for preparing a the light transmitting porous conductive material of claim 1 comprising the steps of: (1) forming a conductive oxide film on the surfaces inside the pores of a porous glass, and (2) forming a conductive oxide film on the outer surfaces of the porous glass.

9. **(Currently Amended)** The method according to claim 8, wherein any a method selected from the group consisting of the following methods (i) to (v) is employed in the step (1) of forming a conductive oxide film on the surfaces inside the pores of the porous glass: (i) a chemical vapor deposition method, (ii) a sputtering method, (iii) an impregnation method, (iv) a method wherein silanol groups present on the surface of the porous glass are reacted with an organic metal compound under high vacuum and the reaction product is then oxidized by heating in air, and (v) a method wherein a mixture of a polymer or an amine group-containing organic metal compound with a raw material for the film is applied to the surface of the porous glass and then the polymer or the organic compound is removed by heating in air.

10. **(Original)** The method according to claim 8, wherein any method selected from the group consisting of the following methods (i), (ii) and (v) is employed in the step (2) of forming a conductive oxide film on the outer surfaces of the porous glass: (i) a chemical vapor deposition method, (ii) a sputtering method, and (v) a method wherein a mixture of a polymer or an amine group-containing organic metal compound with a raw material for the film is applied to the surface of the porous glass and then the polymer or the organic compound is removed by heating in air.

11. **(Original)** The method according to claim 8, wherein any method selected from the group consisting of the following methods (i), (iv) and (v) is employed in the step (1) of forming a conductive oxide film on the surfaces inside the pores of the porous glass: (i) a chemical vapor deposition method, (iv) a method wherein silanol groups present on the surface of the porous glass are reacted with an organic metal compound under high vacuum and the reaction product is then oxidized by heating in air, and (v) a method wherein a mixture of a polymer or an amine group-containing organic metal compound with a raw material for the film is applied to the surface of the porous glass and then the polymer or the organic compound is removed by heating in air, and wherein the method (i) or (v) is employed in the step (2) of forming a conductive oxide film on the outer surfaces of the porous glass: (i) a chemical vapor deposition method, or (v) a method wherein a mixture of a polymer or an amine group-containing organic metal compound with a raw material for the film is applied to the surface of the porous glass and then the polymer or the organic compound is removed by heating in air.